## ABSTRACT OF THE DISCLOSURE (FIG. 45)

"SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME"

In the present invention, the bonding pad is formed in a lattice-like shape. Directly underneath the passivation layer, the etching stopper layer is provided. An opening is made through the passivation layer and the etching stopper layer so as to expose the bonding pad. The cavity sections of the lattice-like shape of the bonding pad are filled with the insulating layer. The bonding wire is connected to the lattice-shaped bonding pad. With this structure, the bonding error of the device manufactured by the damascening process can be avoided.